

isc N-Channel MOSFET Transistor

IPB026N06N

• FEATURES

- With TO-263(D2PAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

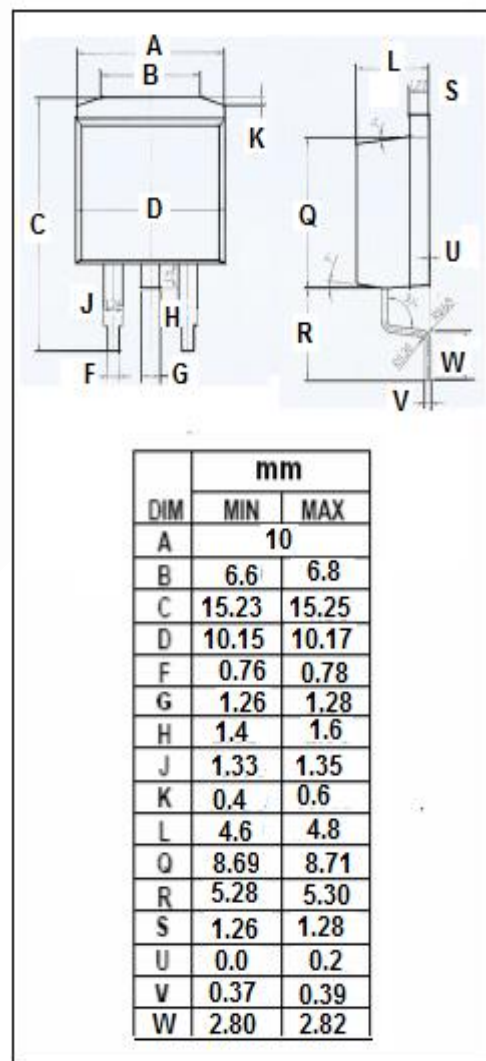
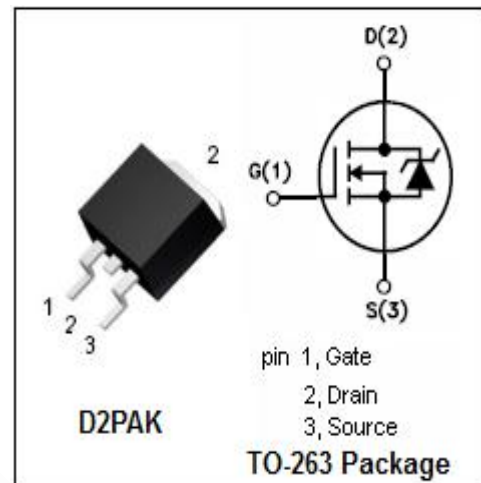
- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous; $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	100	A
I_{DM}	Drain Current-Single Pulsed	400	A
P_D	Total Dissipation	136	W
T_j	Operating Junction Temperature	175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~175	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	1.1	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	40	$^{\circ}\text{C/W}$



isc N-Channel MOSFET Transistor**IPB026N06N****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =0.075mA	2.1		3.3	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =100A		2.3	2.6	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V; V _{GS} = 0V; T _c =25°C V _{DS} =60V; V _{GS} = 0V; T _c =125°C			1 100	μA
V _{SDF}	Diode forward voltage	I _{SD} =100A, V _{GS} = 0 V			1.2	V